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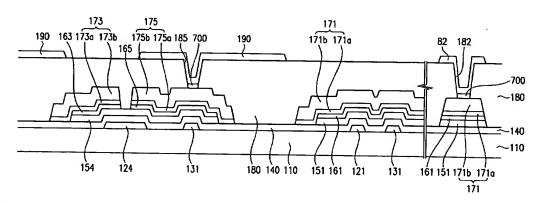
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(54) Title: CONTACT PORTION AND MANUFACTURING METHOD THEREOF, THIN FILM TRANSISTOR ARRAY PANEL AND MANUFACTURING METHOD THEREOF



(57) Abstract: A method of manufacturing a contact portion is provided, which includes: forming a first signal line on a substrate (110), forming a insulating layer (140) covering the first signal line and having a contact hole (182, 185) exposing the first signal line; forming a contact layer (700) on the exposed surface of the first signal through the contact hole; and forming a second signal line (82, 190) connected to the first signal line via the contact layer. Wherein the first signal line is made of Al or Al alloy, and the second signal line is made of ITO or IZO.